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## Correction: Integration of BiFeO<sub>3</sub>/La<sub>0.7</sub>Sr<sub>0.3</sub>MnO<sub>3</sub> heterostructures with III–V semiconductors for low-power non-volatile memory and multiferroic field effect transistors

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Correction for 'Integration of BiFeO<sub>3</sub>/La<sub>0.7</sub>Sr<sub>0.3</sub>MnO<sub>3</sub> heterostructures with III–V semiconductors for low-power non-volatile memory and multiferroic field effect transistors' by Md. Shafiqur Rahman *et al.*, *J. Mater. Chem. C*, 2016, 4, 10386–10394.

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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